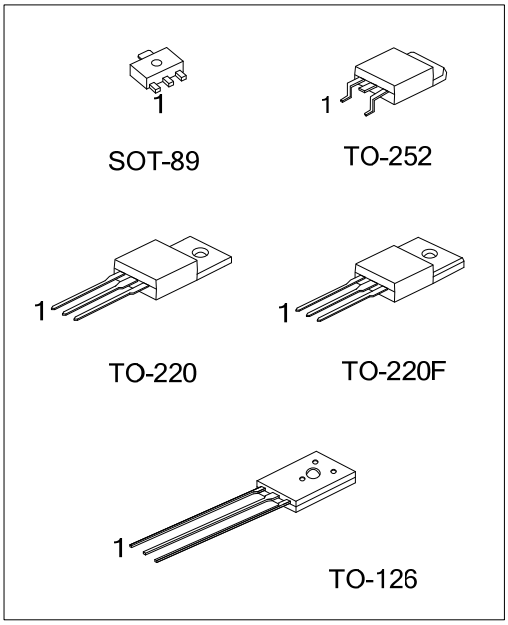
2SB834

PNP SILICON TRANSISTOR

HIGH VOLTAGE TRANSISTOR



■ DESCRIPTION

Low frequency power amplifier applications.

■ ORDERING INFORMATION

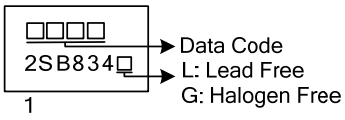
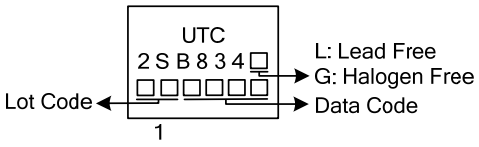
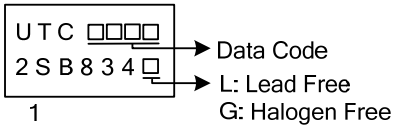
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SB834L-x-AB3-R	2SB834G-x-AB3-R	SOT-89	B	C	E	Tape Reel
2SB834L-x-T60-K	2SB834G-x-T60-K	TO-126	E	C	B	Bulk
2SB834L-x-TA3-T	2SB834G-x-TA3-T	TO-220	B	C	E	Tube
2SB834L-x-TF3-T	2SB834G-x-TF3-T	TO-220F	B	C	E	Tube
2SB834L-x-TN3-R	2SB834G-x-TN3-R	TO-252	B	C	E	Tape Reel

Note: Pin Assignment: B: Base C: Collector E: Emitter

2SB834L-x-AB3-R
(1)Packing Type
(2)Package Type
(3)Rank
(4)Lead Plating

(1) K: Bulk, T: Tube, R: Tape Reel
(2) AB3: SOT-89, T60: TO-126, TA3: TO-220, TF3: TO-220F, TN3: TO-252
(3) x: refer to Classification of h_{FE1}
(4) L: Lead Free, G: Halogen Free

■ MARKING INFORMATION

PACKAGE	MARKING
SOT-89	
TO-220 TO-220F TO-252	
TO-126	

■ ABSOLUTE MAXIMUM RATINGS (Operating temperature range applies unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	-60	V
Collector-Emitter Voltage		V_{CEO}	-60	V
Emitter-Base Voltage		V_{EBO}	-7	V
Collector Current		I_C	-3	A
Base Current		I_B	-0.5	A
Power Dissipation (T_C=25°C)	SOT-89	P_D	3	W
	TO-220		30	W
	TO-252		26	W
	TO-126/TO-220F		25	W
Junction Temperature		T_J	+125	°C
Storage Temperature		T_{STG}	-40 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=-50mA	-60			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-60V			-100	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-7V			-100	μA
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I_C=-3A, I_B=0.3A			-1	V
Base-Emitter On Voltage	$V_{BE(ON)}$	V_{CE}=-5V, I_C=-0.5A		-0.7	-1	V
DC Current Gain	h_{FE1}	I_C=-0.5A, V_{CE}=-5V	60		300	
	h_{FE2}	I_C=-3A, V_{CE}=-5V	20			
Current Gain Bandwidth Product	f_T	V_{CE}=-5V, I_C=-0.5A		9		MHZ

■ CLASSIFICATION of h_{FE1}

RANK	O	Y	GR
RANGE	60-120	100-200	150-300

■ TYPICAL CHARACTERISTICS